

**AMENDMENTS TO THE CLAIMS**

Please amend the Claims as follows. Insertions are shown underlined while deletions are ~~struck through~~.

1 (currently amended): A polishing pad used in chemical mechanical polishing and having a polishing region and a light-transmitting region, said polishing pad having at least one of the following characteristics: i) wherein the light transmittance ~~of~~in the light-transmitting region ~~over~~throughout the wavelength range of 400 to 700 nm is 50% or more; ii) a thickness of the light-transmitting region is 0.5 to 4 mm, and light transmittance in the light-transmitting region throughout the wavelength range of 600 to 700 nm is 80% or more; or iii) the light-transmitting region is arranged between a central portion and a peripheral portion of the polishing pad, and a length (D) in a diametrical direction is 3 times or more longer than a length (L) in a circumferential direction.

2 (currently amended): The polishing pad according to claim 1, wherein ~~the~~a rate of change of the light transmittance ~~of~~in the light-transmitting region in wavelengths of 400 to 700 nm represented by the following equation is 50% or less:

the rate of change (%) = {(maximum transmittance in 400 to 700 nm – minimum transmittance in 400 to 700 nm)/maximum transmittance in 400 to 700 nm}×100.

3 (currently amended): The polishing pad according to claim 1 ~~or~~2, wherein the light transmittance ~~of~~in the light-transmitting region at a wavelength of 400 nm is 50% or more, and the transmittance ~~of~~in the light-transmitting region ~~over~~throughout the wavelength range of 500 to 700 nm is 90% or more.

4 (currently amended): The polishing pad according to any one of claims 1 ~~to~~3, wherein ~~the~~a difference among ~~the~~ respective light transmittances ~~of~~in the light-transmitting region in 500 to 700 nm is 5% or less.

5-6 (canceled)

7 (currently amended): The polishing pad according to claim ~~6~~1, wherein ~~the~~a shape of the light-transmitting region is rectangular.

8 (currently amended): The polishing pad according to claim ~~16~~or 7, wherein ~~a~~the length (D) in ~~the~~a diametrical direction is 1/4 to 1/2 relative to ~~the~~a diameter of a material to be polished.

9 (currently amended): The polishing pad according to ~~any one of claims 1 to 8~~, wherein ~~the~~ scatter of the thickness of the light-transmitting region is 100  $\mu\text{m}$  or less.

10 (currently amended): The polishing pad according to ~~any one of claims 1 to 9~~, wherein materials for forming the polishing region and the light-transmitting region are polyurethane resin.

11 (original): The polishing pad according to claim 10, wherein the polyurethane resin as the material for forming the polishing region and the polyurethane resin as the material for forming the light-transmitting region comprise the same kinds of organic isocyanate, polyol and chain extender.

12 (currently amended): The polishing pad according to ~~any one of claims 1 to 11~~, wherein ~~the~~ material for forming the light-transmitting region is non-foam.

13 (currently amended): The polishing pad according to ~~any one of claims 1 to 12~~, which does not have an uneven structure for retaining and renewing an abrasive liquid on ~~the~~ surface of the light-transmitting region ~~in the~~ on a polishing side.

14 (currently amended): The polishing pad according to ~~any one of claims 1 to 13~~, wherein ~~the~~ material for forming the polishing region is fine-cell foam.

15 (currently amended): The polishing pad according to ~~any one of claims 1 to 14~~, wherein ~~the~~ surface of the polishing region ~~in the~~ on a polishing side is provided with grooves.

16 (currently amended): The polishing pad according to claim 14 ~~or 15~~, wherein ~~the~~ average cell diameter of the fine-cell foam is 70  $\mu\text{m}$  or less.

17 (currently amended): The polishing pad according to ~~any one of claims 14 to 16~~, wherein ~~the~~ specific gravity of the fine-cell foam is 0.5 to 1.0  $\text{g}/\text{cm}^3$ .

18 (currently amended): The polishing pad according to ~~any one of claims 14 to 17~~, wherein ~~the~~ hardness of the fine-cell foam is 45 to 65° in terms of Asker D hardness.

19 (currently amended): The polishing pad according to ~~any one of claims 14 to 18~~, wherein ~~the~~ compressibility of the fine-cell foam is 0.5 to 5.0%.

20 (currently amended): The polishing pad according to ~~any one of claims 14 to 19~~, wherein ~~the~~ compression recovery of the fine-cell foam is 50 to 100%.

21 (currently amended): The polishing pad according to ~~any one of claims 14 to 20~~, wherein ~~the~~ storage elastic modulus of the fine-cell foam at 40°C at 1 Hz is 200 MPa or more.

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22 (currently amended): A method of producing a semiconductor device, which comprises a step of polishing ~~the~~a surface of a semiconductor wafer with the polishing pad ~~described~~recited in ~~any one of claims 1 to 21.~~